

## HAT2026R

Silicon N Channel Power MOS FET  
High Speed Power Switching

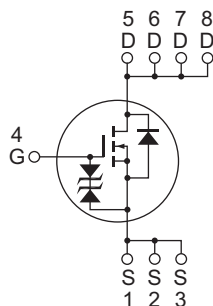
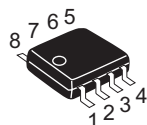
REJ03G1161-0500  
(Previous: ADE-208-523C)  
Rev.5.00  
Sep 07, 2005

### Features

- Low on-resistance
- Capable of 2.5 V gate drive
- Low drive current
- High density mounting

### Outline

RENESAS Package code: PRSP0008DD-D  
(Package name: SOP-8 <FP-8DAV> )



1, 2, 3 Source  
4 Gate  
5, 6, 7, 8 Drain

## Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Value	Unit
Drain to source voltage	V <sub>DSS</sub>	20	V
Gate to source voltage	V <sub>GSS</sub>	±12	V
Drain current	I <sub>D</sub>	11	A
Drain peak current	I <sub>D (pulse)</sub> <sup>Note 1</sup>	88	A
Body-drain diode reverse drain current	I <sub>DR</sub>	11	A
Channel dissipation	P <sub>ch</sub> <sup>Note 2</sup>	2.5	W
Channel temperature	T <sub>ch</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C

Notes: 1. PW ≤ 10 μs, duty cycle ≤ 1%

2. When using the glass epoxy board (FR4 40 × 40 × 1.6 mm), PW ≤ 10 s

## Electrical Characteristics

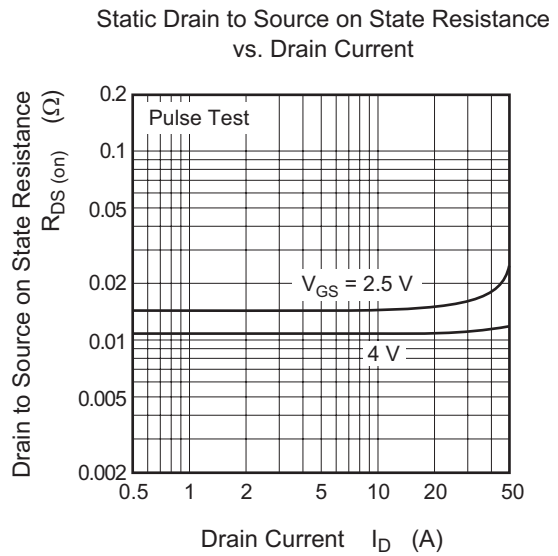
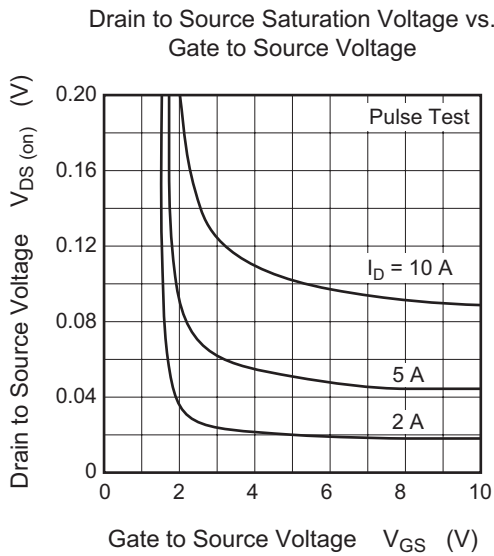
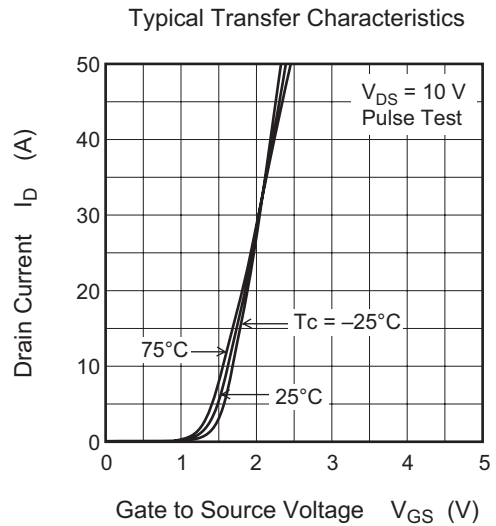
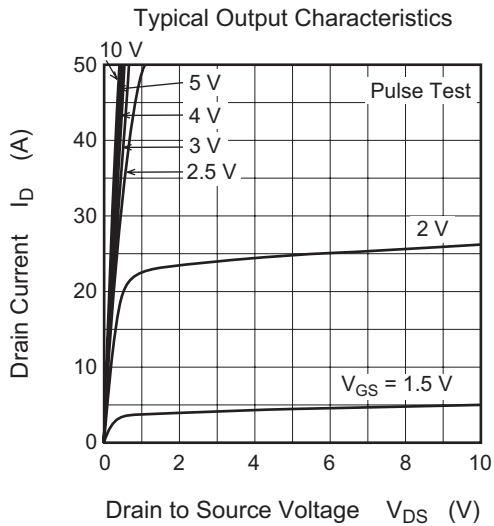
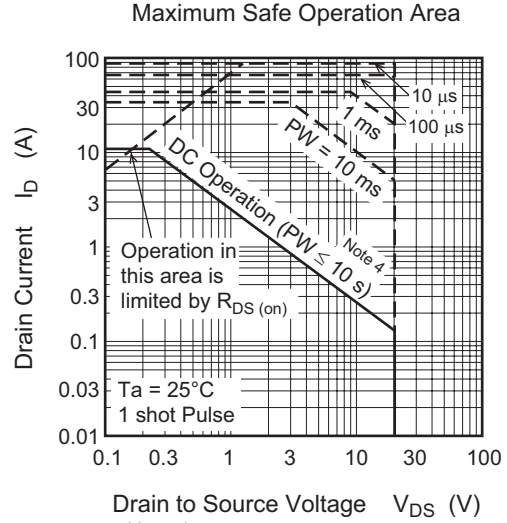
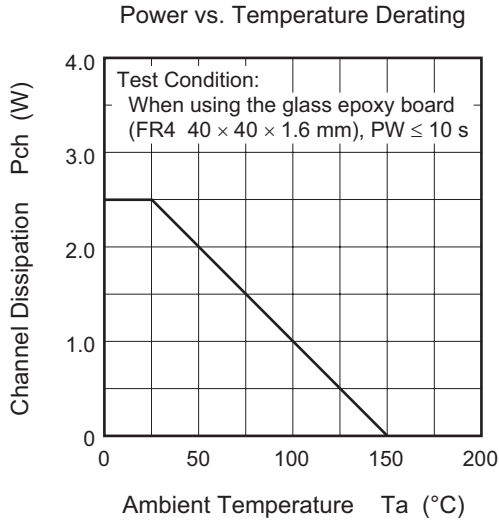
(Ta = 25°C)

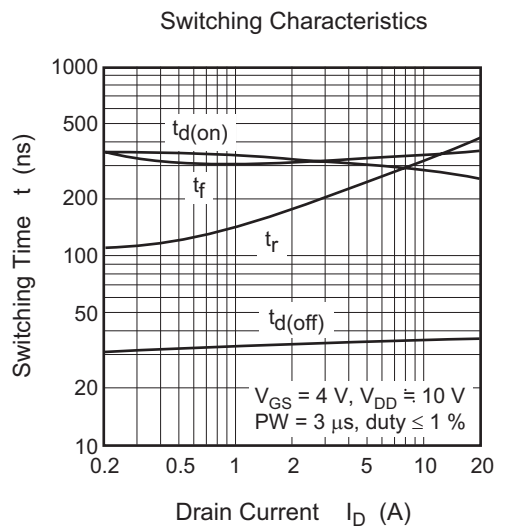
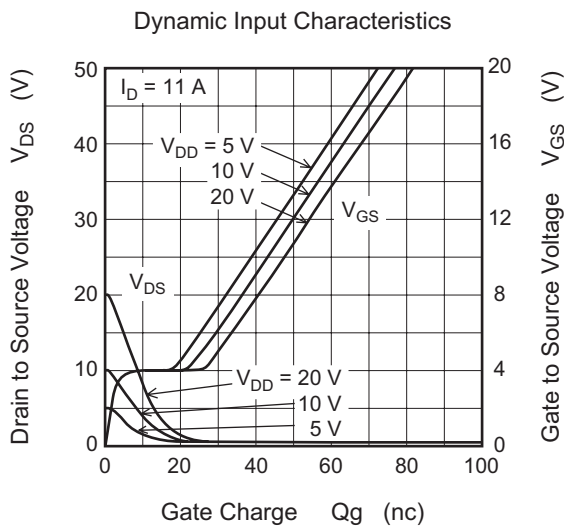
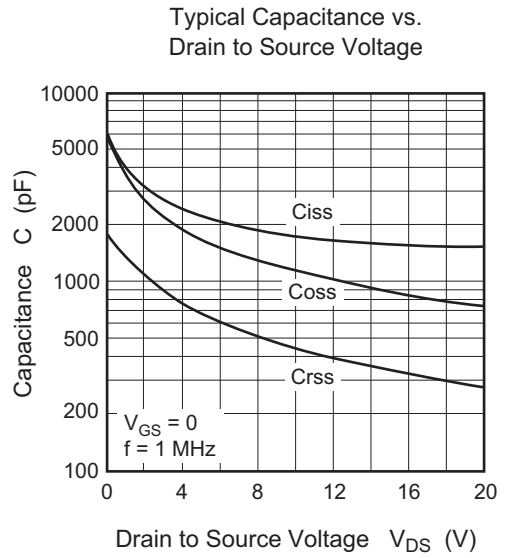
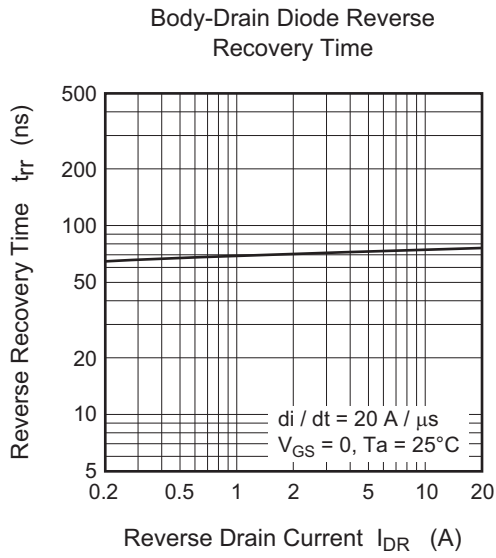
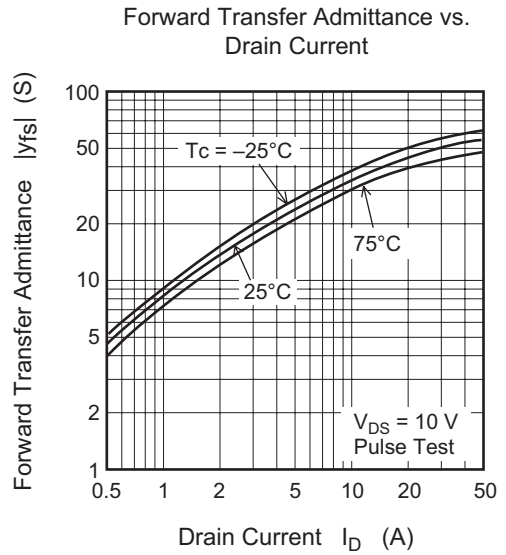
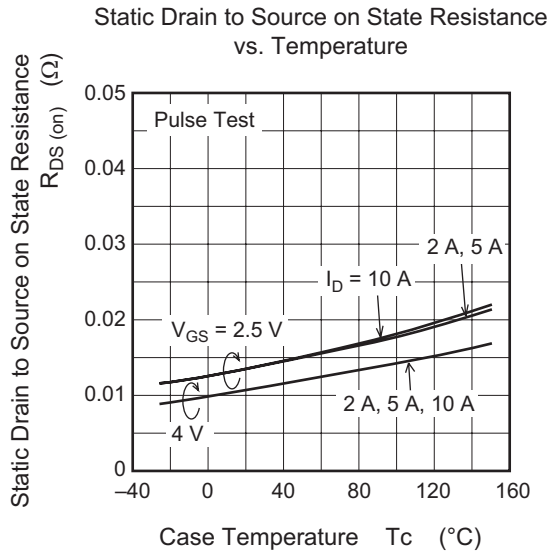
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	V <sub>(BR) DSS</sub>	20	—	—	V	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0
Gate to source breakdown voltage	V <sub>(BR) GSS</sub>	±12	—	—	V	I <sub>G</sub> = ±100 μA, V <sub>DS</sub> = 0
Gate to source leak current	I <sub>GSS</sub>	—	—	±10	μA	V <sub>GS</sub> = ±10 V, V <sub>DS</sub> = 0
Zero gate voltage drain current	I <sub>DSS</sub>	—	—	1	μA	V <sub>DS</sub> = 20 V, V <sub>GS</sub> = 0
Gate to source cutoff voltage	V <sub>GS (off)</sub>	0.4	—	1.4	V	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1 mA
Static drain to source on state resistance	R <sub>DS (on)</sub>	—	0.011	0.015	Ω	I <sub>D</sub> = 6 A, V <sub>GS</sub> = 4 V <sup>Note 3</sup>
	R <sub>DS (on)</sub>	—	0.014	0.021	Ω	I <sub>D</sub> = 6 A, V <sub>GS</sub> = 2.5 V <sup>Note 3</sup>
Forward transfer admittance	y <sub>fs</sub>	18	27	—	S	I <sub>D</sub> = 6 A, V <sub>DS</sub> = 10 V <sup>Note 3</sup>
Input capacitance	C <sub>iss</sub>	—	1760	—	pF	V <sub>DS</sub> = 10 V V <sub>GS</sub> = 0 f = 1 MHz
Output capacitance	C <sub>oss</sub>	—	1130	—	pF	
Reverse transfer capacitance	C <sub>rss</sub>	—	450	—	pF	
Turn-on delay time	t <sub>d (on)</sub>	—	35	—	ns	V <sub>GS</sub> = 4 V, I <sub>D</sub> = 6 A, V <sub>DD</sub> ≅ 10 V
Rise time	t <sub>r</sub>	—	275	—	ns	
Turn-off delay time	t <sub>d (off)</sub>	—	300	—	ns	
Fall time	t <sub>f</sub>	—	340	—	ns	
Body-drain diode forward voltage	V <sub>DF</sub>	—	0.83	1.08	V	I <sub>F</sub> = 11 A, V <sub>GS</sub> = 0 <sup>Note 3</sup>
Body-drain diode reverse recovery time	t <sub>rr</sub>	—	75	—	ns	I <sub>F</sub> = 11 A, V <sub>GS</sub> = 0 di <sub>F</sub> /dt = 20 A/μs

Note: 3. Pulse test

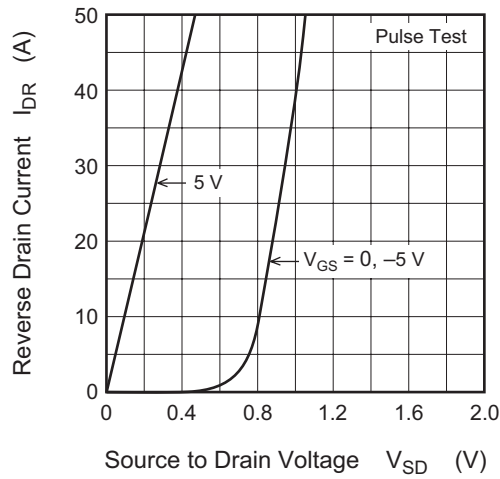
The specifications may be change without notice.

### Main Characteristics

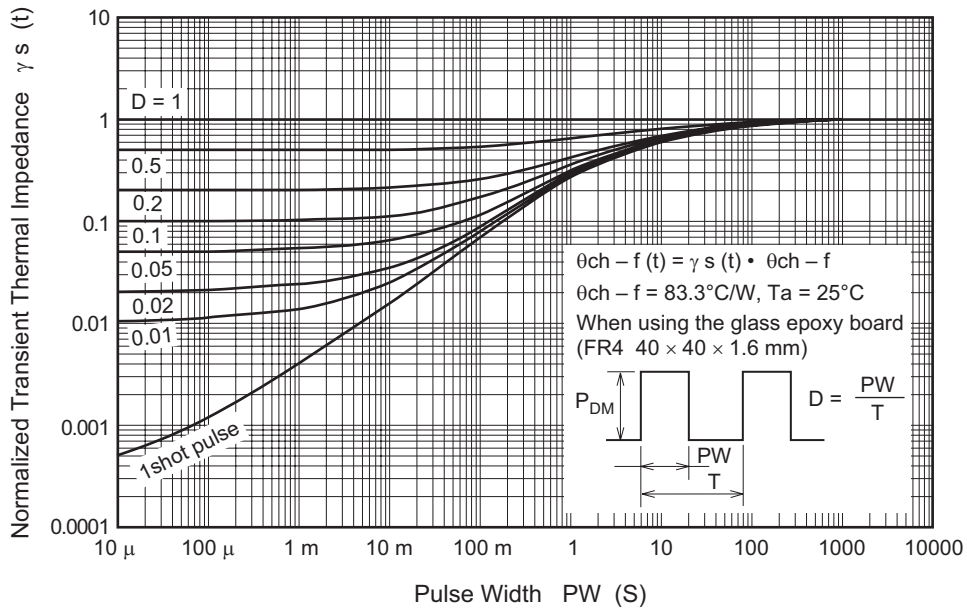




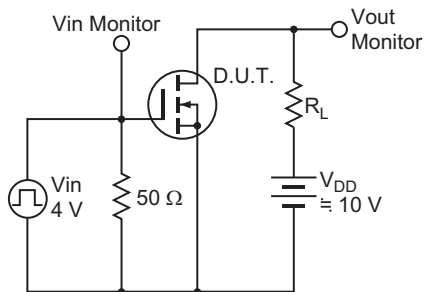
Reverse Drain Current vs. Source to Drain Voltage



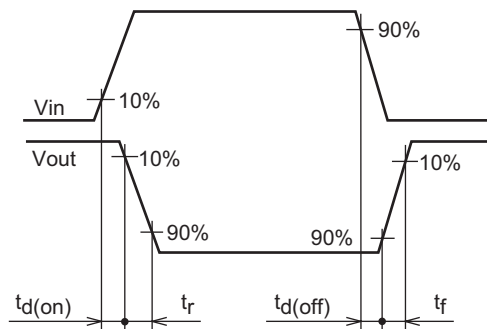
Normalized Transient Thermal Impedance vs. Pulse Width



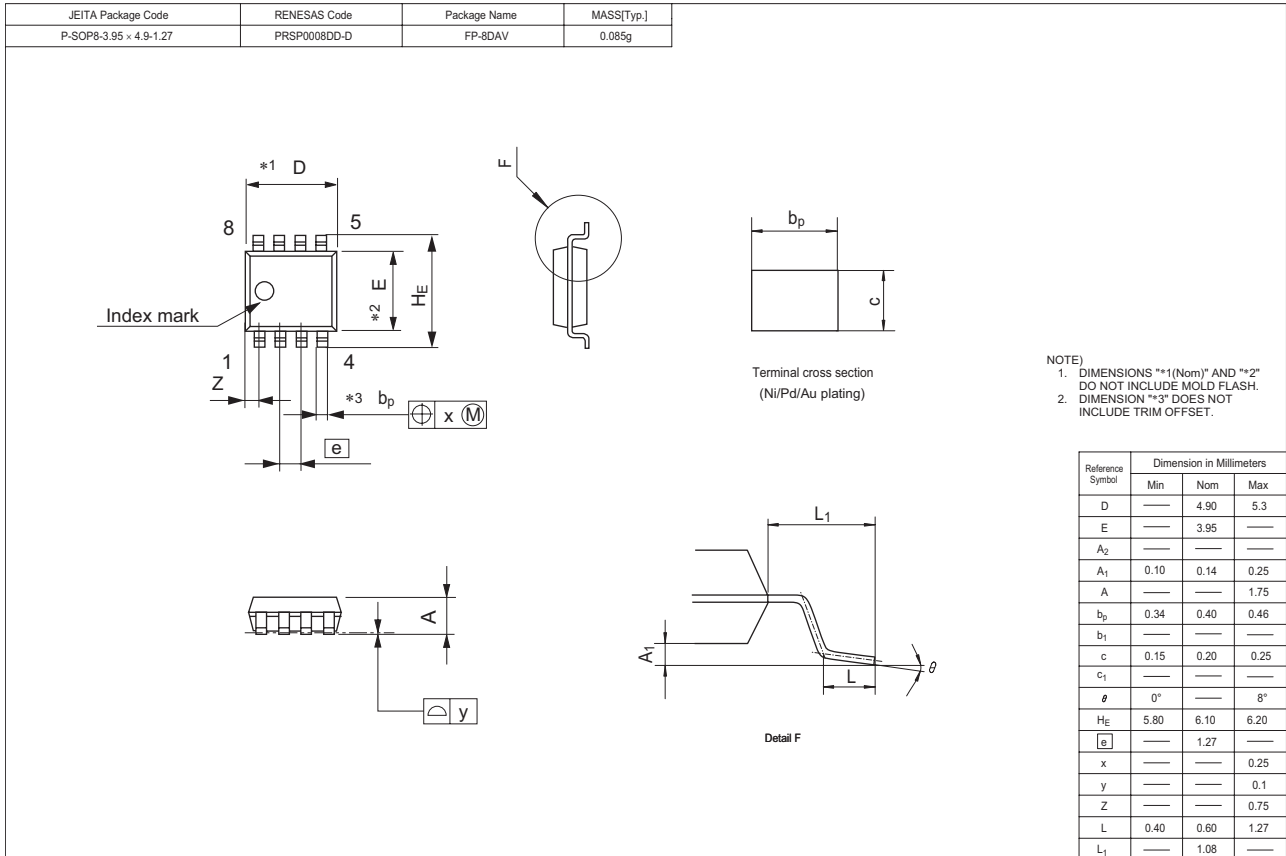
Switching Time Test Circuit



Switching Time Waveform



### Package Dimensions



### Ordering Information

Part Name	Quantity	Shipping Container
HAT2026R-EL-E	2500 pcs	Taping

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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